

Transistors with Built-in Resistor DRA5113Z0L

DRA5113Z0L Silicon PNP epitaxial planar type

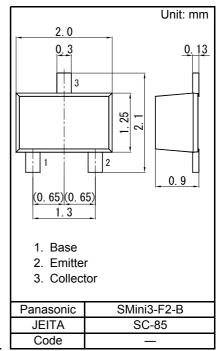
For digital circuits Complementary to DRC5113Z DRA2113Z in SMini3 type package

Features

- Low collector-emitter saturation voltage Vce(sat)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)
- Marking Symbol: L1

Packaging

Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)



Unit	-			
V		_		
V	Internal	Con	nectior	ר
mA				
mW	R_1	Г	OC	
°C	B O-	r K		
°C	R ₂]	• 5	
°C		•	oE	
	Resistance	R1	1	kΩ
	value	R2	10	kΩ

Absolute Maximum R	Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	VCBO	-50	V
Collector-emitter voltage (Base open)	VCEO	-50	V
Collector current	IC	-100	mA
Total power dissipation	PT	150	mW
Junction temperature	Tj	150	°C
Operating ambient temperature	Topr	-40 to +85	°C
Storage temperature	Tstg	-55 to +150	С°

Electrical Characteristics	5 Ta = 25 °C ± 3 °C
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Symbol	Conditions	Min	Тур	Max	Unit
VCBO	IC = -10 μA, IE = 0	-50			V
VCEO	IC = -2 mA, IB = 0	-50			V
ICBO	VCB = -50 V, IE = 0			-0.1	μA
ICEO	VCE = -50 V, IB = 0			-0.5	μA
IEBO	VEB = -6 V, IC = 0			-1.5	mA
hFE	VCE = -10 V, IC = -5 mA	30			-
VCE(sat)	IC = -10 mA, IB = -0.5 mA			-0.25	V
Vi(on)	VCE = -0.2 V, IC = -5 mA	-1.0			V
Vi(off)	VCE = -5 V, IC = -100 μA			-0.4	V
R1		-30%	1	+30%	kΩ
R1/R2		0.08	0.1	0.12	-
	VCBO VCEO ICBO IEBO hFE VCE(sat) Vi(on) Vi(off) R1	$\begin{array}{c c} VCBO & IC = -10 \ \mu\text{A}, IE = 0 \\ \hline VCEO & IC = -2 \ m\text{A}, IB = 0 \\ \hline ICBO & VCB = -50 \ V, IE = 0 \\ \hline ICEO & VCE = -50 \ V, IB = 0 \\ \hline IEBO & VEB = -6 \ V, IC = 0 \\ \hline hFE & VCE = -10 \ V, IC = -5 \ m\text{A} \\ \hline VCE(sat) & IC = -10 \ m\text{A}, IB = -0.5 \ m\text{A} \\ \hline Vi(on) & VCE = -0.2 \ V, IC = -5 \ m\text{A} \\ \hline Vi(off) & VCE = -5 \ V, IC = -100 \ \mu\text{A} \\ \hline R1 \\ \hline \end{array}$	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	VCBO IC = -10 μ A, IE = 0 -50 VCEO IC = -2 mA, IB = 0 -50 ICBO VCB = -50 V, IE = 0 -50 ICEO VCE = -50 V, IB = 0 -50 IEBO VEB = -6 V, IC = 0 -50 hFE VCE = -10 V, IC = -5 mA 30 VCE(sat) IC = -10 mA, IB = -0.5 mA -1.0 Vi(on) VCE = -5 V, IC = -5 mA -1.0 Vi(off) VCE = -5 V, IC = -100 μ A -30%	VCBO IC = -10 μ A, IE = 0 -50 -50 VCEO IC = -2 mA, IB = 0 -50 -50 ICBO VCB = -50 V, IE = 0 -0.1 ICEO VCE = -50 V, IB = 0 -0.5 IEBO VEB = -6 V, IC = 0 -1.5 hFE VCE = -10 V, IC = -5 mA 30 VCE(sat) IC = -10 mA, IB = -0.5 mA -0.25 Vi(on) VCE = -0.2 V, IC = -5 mA -1.0 Vi(off) VCE = -5 V, IC = -100 μ A -0.4 R1 -30% 1

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

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IB = -800 μA

-700 µA

-600 µA

-500 uA -400 µA

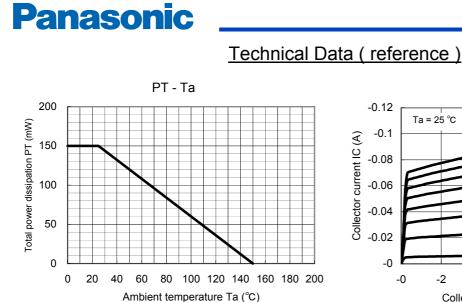
-300 µA

-200 µA

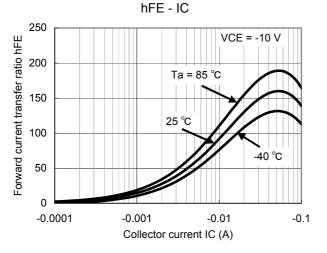
-100 µA

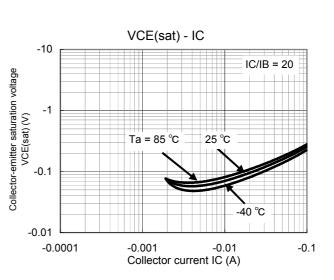
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-10









IC - VCE

Ta = 25 °C

-2

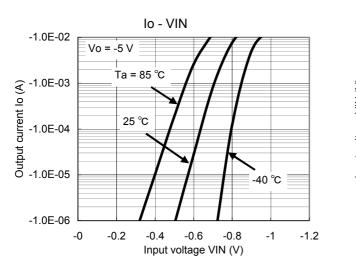
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-6

Collector-emitter voltage VCE (V)

-8

-0



VIN - Io -100 Vo = -0.2 V Input voltage VIN (V) -10 25 °C Ta = -40 °C -1 85 °C -0.1 -0.0001 -0.001 -0.01 -0.1 Output current Io (A)

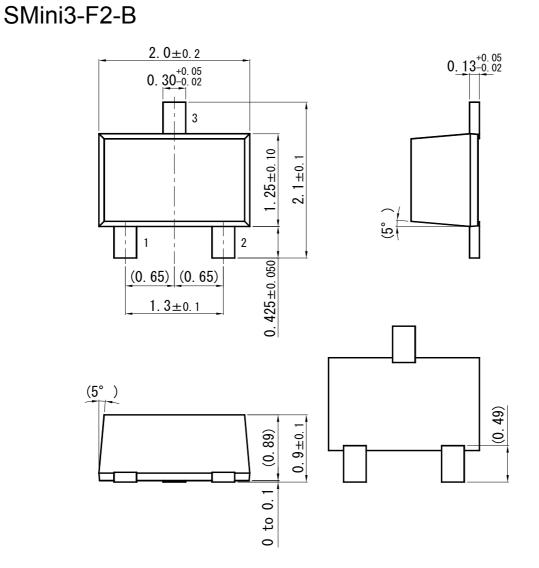
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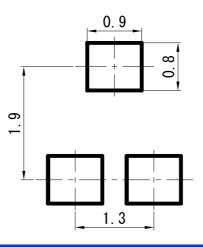


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Unit: mm



Land Pattern (Reference) (Unit: mm)



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